Product data sheet

1. General description

Silicon Carbide Schottky diode in a TSPAK plastic package, featured with top side cooling structure, designed for high frequency, high efficiency systems.





2. Features and benefits

- Top side cooling structure
- New 6th Generation Technology
- Low Forward Voltage Drop
- Low Reverse Leakage Current
- High Forward Surge Capability I_{FSM}
- · Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant



3. Applications

- PC/Telecom/Server SMPS
- UPS & energy storage systems
- · Battery formation systems
- EV chargers
- PV inverter and MPPT circuit
- Motor Drives

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Values | | | Unit |
|----------------|---------------------------------|--|--------|------|------|------|
| Absolute | maximum rating | | | | | |
| V_{RRM} | repetitive peak reverse voltage | | 650 | | V | |
| I _F | continuous forward current | T _{mb} ≤ 149 °C, DC; <u>Fig. 2</u> | 10 | | А | |
| T _j | junction temperature | | 175 | | °C | |
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static ch | aracteristics | | | | | |
| V _F | forward voltage | I _F = 10 A; T _j = 25 °C; <u>Fig. 5</u> | - | 1.29 | 1.45 | V |
| | | I _F = 10 A; T _j = 150 °C; <u>Fig. 5</u> | - | 1.45 | 1.65 | V |
| Dynamic | characteristics | | | | | |
| Q _r | recovered charge | $I_F = 10 \text{ A}; dI_F/dt = 500 \text{ A/}\mu\text{s}; V_R = 400 \text{ V};$ $T_i = 25 ^{\circ}\text{C}; Fig. 7$ | - | 24 | - | nC |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----------|--------|-------------------------------------|---------------------|---|
| 1-2 | n.c | n.c | | K 14 A |
| 3-7 | Α | anode | 8 | K - |
| 8-9 mb | К | mounting base; connected to cathode | MB MB 7 6 5 4 3 2 1 | |

6. Ordering information

Table 3. Ordering information

| Type number | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|---------------|--------------|-----------------------|-------------------|------------------------|-----------------|--------------------|
| WNSC6D10650TB | TSPAK | WNSC6D10650TB6J | Reel | 600 | TSPAK | 06-Dec-2024 |

7. Marking

Table 4. Marking codes

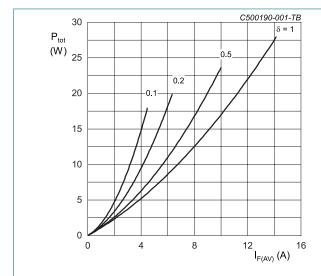
| Type number | Marking codes |
|---------------|---------------|
| WNSC6D10650TB | WNSC6D |
| | 10650TB |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Notes | Values | Unit |
|------------------|-------------------------------------|--|-------|------------|------------------|
| V_{RRM} | repetitive peak reverse voltage | | | 650 | V |
| V_{RWM} | crest working reverse voltage | | | 650 | V |
| V_R | reverse voltage | DC | | 650 | V |
| I _F | continuous forward | T _{mb} ≤ 149 °C, DC; <u>Fig. 2</u> | | 10 | А |
| | current | T _{mb} ≤ 125 °C, DC; <u>Fig. 2</u> | | 16 | Α |
| | | T _{mb} ≤ 25 °C, DC; <u>Fig. 2</u> | | 31 | Α |
| I _{FRM} | repetitive peak forward current | δ = 0.5; t _p = 25 μs; T _{mb} ≤ 125 °C; square-wave pulse | | 25 | А |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | | 70 | Α |
| | | t_p = 10 μ s; $T_{j(init)}$ = 25 °C; square-wave pulse | | 665 | Α |
| l ² t | I ² t for fusing | t _p = 10 ms; SIN | | 24.5 | A ² s |
| T _{stg} | storage temperature | | | -55 to 175 | °C |
| T _j | junction temperature | | | -55 to 175 | °C |



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 1.036 \text{ V; } R_{\text{s}} = 0.0664 \text{ } \Omega \\ \end{split}$$
 Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

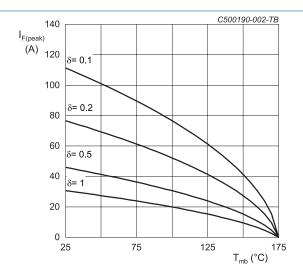
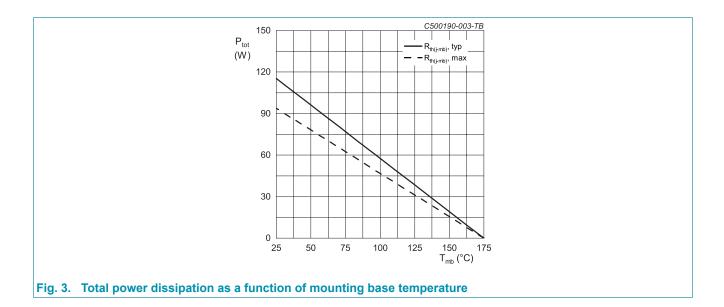


Fig. 2. Current derating as a function of mounting base temperature



9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 4 | - | 1.3 | 1.6 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient free air | in free air | - | 60 | - | K/W |

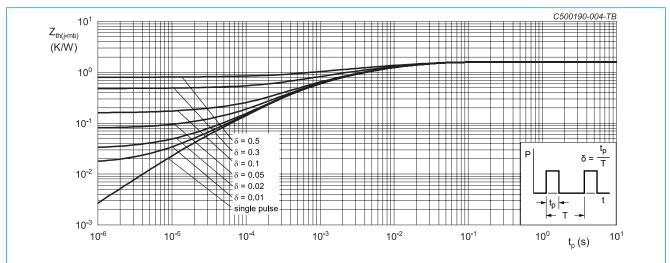
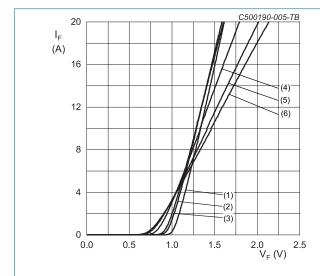


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|---------------------------------|--|-----|------|------|------|
| Static cha | aracteristics | | | | | |
| V _F | forward voltage | I _F = 10 A; T _j = 25 °C; <u>Fig. 5</u> | - | 1.29 | 1.45 | V |
| | | I _F = 10 A; T _j = 150 °C; <u>Fig. 5</u> | - | 1.45 | 1.65 | V |
| | | I _F = 10 A; T _j = 175 °C; <u>Fig. 5</u> | - | 1.50 | 1.70 | V |
| I _R | reverse current | V _R = 650 V; T _j = 25 °C; <u>Fig. 6</u> | - | 1 | 50 | μA |
| | | V _R = 650 V; T _j = 175 °C; <u>Fig. 6</u> | - | 15 | 200 | μA |
| Dynamic | characteristics | | | | | |
| Q_r | recovered charge | $I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$ | - | 24 | - | nC |
| C _d | diode capacitance | f = 1 MHz; V _R = 1 V; T _j = 25 °C | - | 500 | - | pF |
| | | f = 1 MHz; V _R = 300 V; T _j = 25 °C | - | 58 | - | pF |
| | | f = 1 MHz; V _R = 600 V; T _j = 25 °C | - | 52 | - | pF |
| E _{as} | non-repetitive avalanche energy | I _R = 5 A; L = 5 mH; T _{j(init)} = 25 °C | 60 | - | - | mJ |



 $V_o = 1.036 \text{ V}; R_s = 0.0664 \Omega$

(1) $T_j = -55$ °C; typical values (2) $T_j = 0$ °C; typical values

(3) T_i = 25 °C; typical values

(4) T_i = 100 °C; typical values

(5) $T_j = 150$ °C; typical values (6) $T_j = 175$ °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values

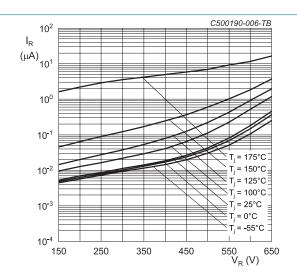
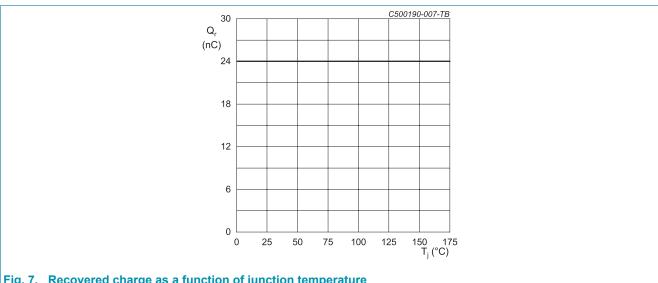
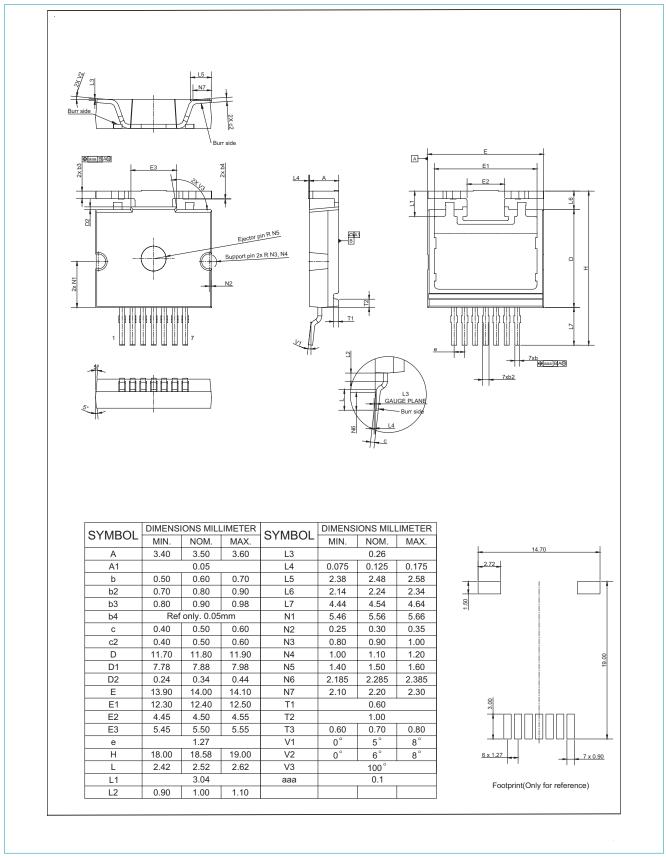


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value



11. Package outline



12. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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WNSC6D10650TB

Silicon Carbide Diode

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13. Contents

| 1. | General description | . 1 |
|-----|-------------------------|-----|
| 2. | Features and benefits | .′ |
| 3. | Applications | .′ |
| 4. | Quick reference data | . 1 |
| 5. | Pinning information | .2 |
| 6. | Ordering information | .2 |
| | Marking | |
| 8. | Limiting values | . 3 |
| 9. | Thermal characteristics | .! |
| 10. | . Characteristics | . (|
| 11. | Package outline | .8 |
| | Legal information | |
| | Contents | |
| | | |

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